

What is claimed is:

1. A semiconductor device comprising a first film and a second film formed in contact with said first film, wherein a concentration of a contaminating impurity in an interface between said first film and said second film is 2×10^{16} atoms/cm³ or less.

2. A device according to claim 1, wherein the contaminating impurity is at least one element selected from periodic table group 1 elements or periodic table group 2 elements.

3. A device according to claim 1, wherein the contaminating impurity element is at least one element selected from the group consisting of Na, K, Mg, Ca, and Ba.

4. A device according to claim 1, wherein said first film and said second film are a crystalline semiconductor film and an insulating film in contact with the crystalline semiconductor film, respectively.

5. A device according to claim 1, wherein said first film and said second film are an insulating film functioning as a gate insulating film and a gate wiring in contact with the insulating film.

6. A semiconductor device comprising a first film, and a second film formed in contact with said first film, wherein a concentration of a contaminating impurity within said first film, a concentration of the contaminating impurity within said second film, and a concentration of the contaminating impurity in the interface between said first

film and said second film are all 2×10^{16} atoms/cm³ or less, respectively.

7. A device according to claim 6, wherein the contaminating impurity is at least one element selected from periodic table group 1 elements or periodic table group 2 elements.

8. A device according to claim 6, wherein the contaminating impurity element is at least one element selected from the group consisting of Na, K, Mg, Ca, and Ba.

9. A device according to claim 6, wherein said first film and said second film are a crystalline semiconductor film and an insulating film in contact with the crystalline semiconductor film, respectively.

10. A device according to claim 6, wherein said first film and said second film are an insulating film functioning as a gate insulating film and a gate wiring in contact with the insulating film.

11. A method of manufacturing a semiconductor device, comprising steps of:
forming a first film;
removing a contaminating impurity from the surface of the first film; and
forming a second film in contact with the first film from the surface of which the contaminating impurity has been removed.

12. A method according to claim 11, wherein the contaminating impurity is at

least one element selected from periodic table group 1 elements or periodic table group 2 elements.

13. A method according to claim 11, wherein the contaminating impurity element
5 is at least one element selected from the group consisting of Na, K, Mg, Ca, and Ba.

14. A method according to claim 11, wherein the contaminating impurity is removed by an acidic solution containing fluorine.

add
Al